74AHC139; 74AHCT139

Dual 2-to-4 line decoder/demultiplexer

Rev. 02 — 9 May 2008 Product data sheet

1. General description

The 74AHC139; 74AHCT139 is a high-speed Si-gate CMOS device and is pin compatible with Low-power Schottky TTL (LSTTL). It is specified in compliance with JEDEC standard No. 7-A.

The 74AHC139; 74AHCT139 is a high-speed, dual 2-to-4 line decoder/demultiplexer. This device has two independent decoders, each accepting two binary weighted inputs (nA0 and nA1) and providing four mutually exclusive active LOW outputs ($n\overline{Y}0$ to $n\overline{Y}3$). Each decoder has an active LOW enable input ($n\overline{E}$). When $n\overline{E}$ is HIGH, every output is forced HIGH. The enable input can be used as the data input for a 1-to-4 demultiplexer application.

The 74AHC139; 74AHCT139 is identical to the HEF4556 of the HE4000B family.

2. Features

- Balanced propagation delays
- All inputs have Schmitt-trigger actions
- Inputs accept voltages higher than V_{CC}
- Input levels:
  - For 74AHC139: CMOS level
  - For 74AHCT139: TTL level
- ESD protection:
  - HBM EIA/JESD22-A114E exceeds 2000 V
  - MM EIA/JESD22-A115-A exceeds 200 V
  - CDM EIA/JESD22-C101C exceeds 1000 V
- Multiple package options
- Specified from –40 °C to +85 °C and from –40 °C to +125 °C

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AHC139				
74AHC139D	–40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74AHC139PW	–40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1

Table 1. Ordering information *…continued*

Type number	Package			
	Temperature range	Name	Description	Version
74AHCT139				
74AHCT139D	–40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74AHCT139PW	–40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1

4. Functional diagram

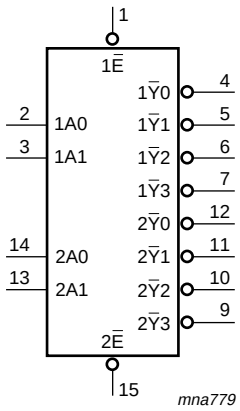
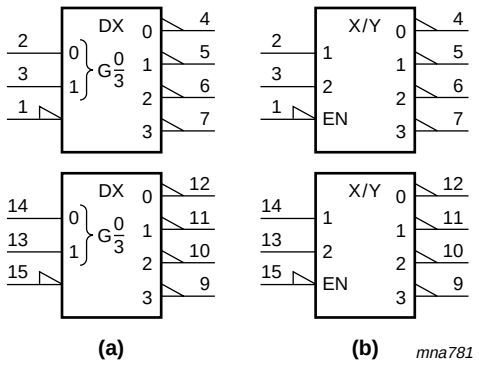


Fig 1. Logic symbol



a = demultiplexer and b = decoder

Fig 2. IEC logic symbol

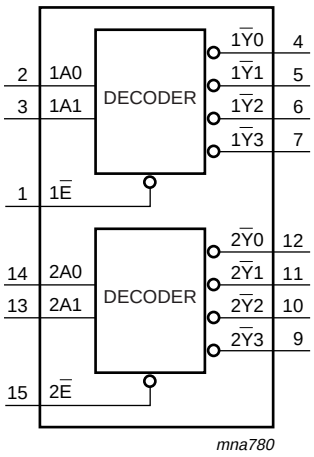


Fig 3. Functional diagram

5. Pinning information

5.1 Pinning

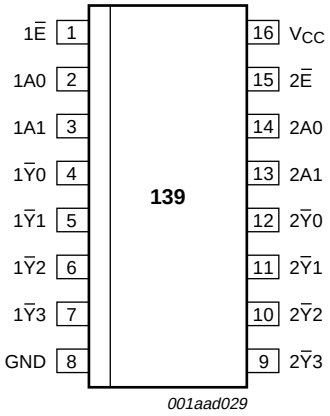


Fig 4. Pin configuration

5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1$\overline{E}$	1	enable input (active LOW)
1A0	2	address input
1A1	3	address input
1$\overline{Y}$0	4	output
1$\overline{Y}$1	5	output
1$\overline{Y}$2	6	output
1$\overline{Y}$3	7	output
GND	8	ground (0 V)
2$\overline{Y}$3	9	output
2$\overline{Y}$2	10	output
2$\overline{Y}$1	11	output
2$\overline{Y}$0	12	output
2A1	13	address input
2A0	14	address input
2$\overline{E}$	15	enable input (active LOW)
V_{CC}	16	supply voltage

6. Functional description

Table 3. Function table[1]

Control	Input		Output			
$n\overline{E}$	nA0	nA1	$n\overline{Y}0$	$n\overline{Y}1$	$n\overline{Y}2$	$n\overline{Y}3$
H	X	X	H	H	H	H
L	L	L	L	H	H	H
	H	L	H	L	H	H
	L	H	H	H	L	H
	H	H	H	H	H	L

[1] H = HIGH voltage level;
L = LOW voltage level;
X = don't care.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			–0.5	+7.0	V
V_I	input voltage			–0.5	+7.0	V
I_{IK}	input clamping current	$V_I < -0.5$ V	[1]	–20	-	mA
I_{OK}	output clamping current	$V_O < -0.5$ V or $V_O > V_{CC} + 0.5$ V	[1]	–20	+20	mA
I_O	output current	$V_O = -0.5$ V to $(V_{CC} + 0.5$ V)		–25	+25	mA
I_{CC}	supply current			-	+75	mA
I_{GND}	ground current			–75	-	mA
T_{stg}	storage temperature			–65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40$ °C to +125 °C	[2]	-	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SO16 packages: above 70 °C the value of P_{tot} derates linearly at 8 mW/K.
For TSSOP16 packages: above 60 °C the value of P_{tot} derates linearly at 5.5 mW/K.

8. Recommended operating conditions

Table 5. Operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
74AHC139						
V_{CC}	supply voltage		2.0	5.0	5.5	V
V_I	input voltage		0	-	5.5	V
V_O	output voltage		0	-	V_{CC}	V
T_{amb}	ambient temperature		–40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 3.0 V to 3.6 V	-	-	100	ns/V
		V_{CC} = 4.5 V to 5.5 V	-	-	20	ns/V
74AHCT139						
V_{CC}	supply voltage		4.5	5.0	5.5	V
V_I	input voltage		0	-	5.5	V
V_O	output voltage		0	-	V_{CC}	V
T_{amb}	ambient temperature		–40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 4.5 V to 5.5 V	-	-	20	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74AHC139										
V_{IH}	HIGH-level input voltage	V_{CC} = 2.0 V	1.5	-	-	1.5	-	1.5	-	V
		V_{CC} = 3.0 V	2.1	-	-	2.1	-	2.1	-	V
		V_{CC} = 5.5 V	3.85	-	-	3.85	-	3.85	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 2.0 V	-	-	0.5	-	0.5	-	0.5	V
		V_{CC} = 3.0 V	-	-	0.9	-	0.9	-	0.9	V
		V_{CC} = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
V_{OH}	HIGH-level output voltage	V_I = V_{IH} or V_{IL}								
		I_O = –50 µA; V_{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I_O = –50 µA; V_{CC} = 3.0 V	2.9	3.0	-	2.9	-	2.9	-	V
		I_O = –50 µA; V_{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I_O = –4.0 mA; V_{CC} = 3.0 V	2.58	-	-	2.48	-	2.40	-	V
		I_O = –8.0 mA; V_{CC} = 4.5 V	3.94	-	-	3.80	-	3.70	-	V
V_{OL}	LOW-level output voltage	V_I = V_{IH} or V_{IL}								
		I_O = 50 µA; V_{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 50 µA; V_{CC} = 3.0 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 50 µA; V_{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 4.0 mA; V_{CC} = 3.0 V	-	-	0.36	-	0.44	-	0.55	V
		I_O = 8.0 mA; V_{CC} = 4.5 V	-	-	0.36	-	0.44	-	0.55	V

Table 6. Static characteristics *…continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
I_I	input leakage current	V_I = 5.5 V or GND; V_{CC} = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	µA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; I_O = 0 A; V_{CC} = 5.5 V	-	-	4.0	-	40	-	80	µA
C_I	input capacitance	$V_I = V_{CC}$ or GND	-	3	10	-	10	-	10	pF
C_O	output capacitance		-	4	-	-	-	-	-	pF
74AHCT139										
V_{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	-	-	2.0	-	2.0	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	-	0.8	-	0.8	-	0.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}; V_{CC} = 4.5 V								
		I_O = –50 µA	4.4	4.5	-	4.4	-	4.4	-	V
		I_O = –8.0 mA	3.94	-	-	3.80	-	3.70	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}; V_{CC} = 4.5 V								
		I_O = 50 µA	-	0	0.1	-	0.1	-	0.1	V
		I_O = 8.0 mA	-	-	0.36	-	0.44	-	0.55	V
I_I	input leakage current	V_I = 5.5 V or GND; V_{CC} = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	µA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; I_O = 0 A; V_{CC} = 5.5 V	-	-	4.0	-	40	-	80	µA
ΔI_{CC}	additional supply current	per input pin; $V_I = V_{CC}$ – 2.1 V; other pins at V_{CC} or GND; I_O = 0 A; V_{CC} = 4.5 V to 5.5 V	-	-	1.35	-	1.5	-	1.5	mA
C_I	input capacitance	$V_I = V_{CC}$ or GND	-	3	10	-	10	-	10	pF
C_O	output capacitance		-	4	-	-	-	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7.

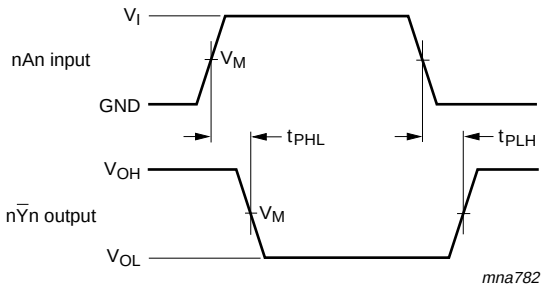
Symbol	Parameter	Conditions		25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
				Min	Typ[1]	Max	Min	Max	Min	Max	
74AHC139											
t_{pd}	propagation delay	nAn to n$\overline{Y}$n; see Figure 5	[2]								
		V_{CC} = 3.0 V to 3.6 V									
		C_L = 15 pF		-	5.5	11.0	1.0	13.0	1.0	14.0	ns
		C_L = 50 pF		-	7.9	14.5	1.0	16.5	1.0	18.5	ns
		V_{CC} = 4.5 V to 5.5 V									
		C_L = 15 pF		-	3.9	7.2	1.0	8.5	1.0	9.0	ns
		C_L = 50 pF		-	5.6	9.2	1.0	10.5	1.0	11.5	ns
		n$\overline{E}$ to n$\overline{Y}$n; see Figure 6	[2]								
		V_{CC} = 3.0 V to 3.6 V									
		C_L = 15 pF		-	4.8	9.2	1.0	11.0	1.0	11.5	ns
		C_L = 50 pF		-	6.9	12.7	1.0	14.5	1.0	16.0	ns
		V_{CC} = 4.5 V to 5.5 V									
		C_L = 15 pF		-	3.4	6.3	1.0	7.5	1.0	8.0	ns
		C_L = 50 pF		-	4.9	8.3	1.0	9.5	1.0	10.5	ns
C_{PD}	power dissipation capacitance	f_i = 1 MHz; V_I = GND to V_{CC}	[3]	-	26	-	-	-	-	-	pF
74AHCT139; V_{CC} = 4.5 V to 5.5 V											
t_{pd}	propagation delay	nAn to n$\overline{Y}$n; see Figure 5	[2]								
		C_L = 15 pF		-	4.7	7.2	1.0	8.5	1.0	9.0	ns
		C_L = 50 pF		-	6.5	9.2	1.0	10.5	1.0	11.5	ns
		n$\overline{E}$ to n$\overline{Y}$n; see Figure 6	[2]								
		C_L = 15 pF		-	3.6	6.3	1.0	7.5	1.0	8.0	ns
		C_L = 50 pF		-	5.2	8.3	1.0	9.5	1.0	10.5	ns
C_{PD}	power dissipation capacitance	f_i = 1 MHz; V_I = GND to V_{CC}	[3]	-	23	-	-	-	-	-	pF

[1] Typical values are measured at nominal supply voltage (V_{CC} = 3.3 V and V_{CC} = 5.0 V).

[2] t_{pd} is the same as t_{PLH} and t_{PHL}.

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in µW).
$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
f_i = input frequency in MHz;
f_o = output frequency in MHz;
C_L = output load capacitance in pF;
V_{CC} = supply voltage in V;
N = number of inputs switching;
$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

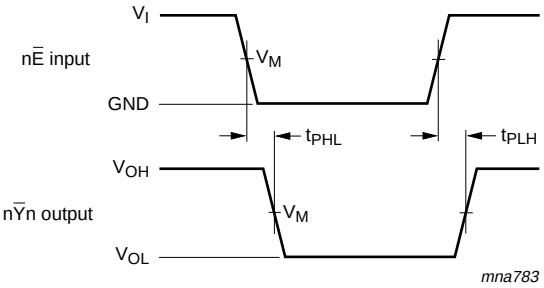
11. Waveforms



Measurement points are given in Table 8.

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 5. Address input to output propagation delays



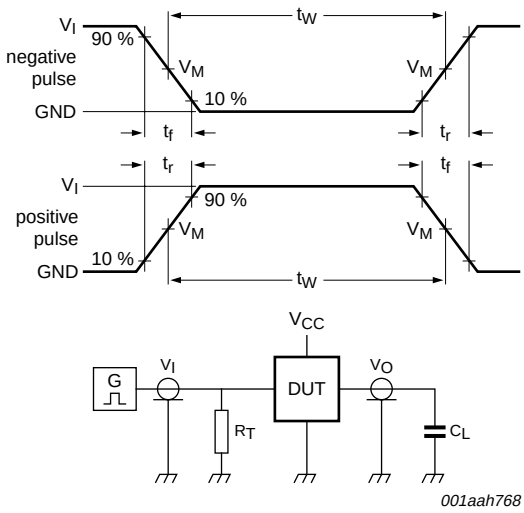
Measurement points are given in Table 8.

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 6. Enable input to output propagation delays

Table 8. Measurement points

Type	Input	Output
	V_M	V_M
74AHC139	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
74AHCT139	1.5 V	$0.5 \times V_{CC}$



Test data is given in Table 9.

Definitions test circuit:

R_T = termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = load capacitance including jig and probe capacitance.

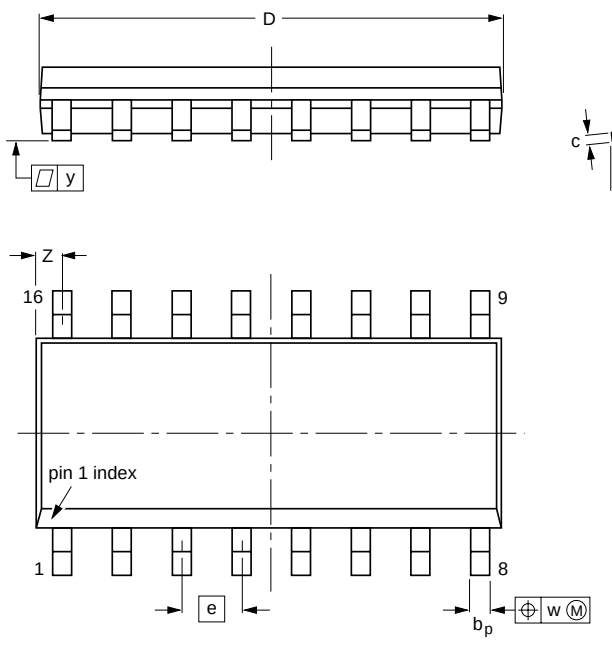
Fig 7. Load circuitry for measuring switching times

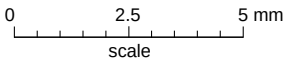
Table 9. Test data

Type	Input		Load	Test
	V_I	t_r, t_f	C_L	
74AHC139	V_{CC}	≤ 3.0 ns	15 pF, 50 pF	t_{PLH}, t_{PHL}
74AHCT139	3.0 V	≤ 3.0 ns	15 pF, 50 pF	t_{PLH}, t_{PHL}

12. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm **SOT109-1**





DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	10.0 9.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8^o 0^o
inches	0.069	0.010 0.004	0.057 0.049	0.01	0.019 0.014	0.0100 0.0075	0.39 0.38	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.020	0.01	0.01	0.004	0.028 0.012	

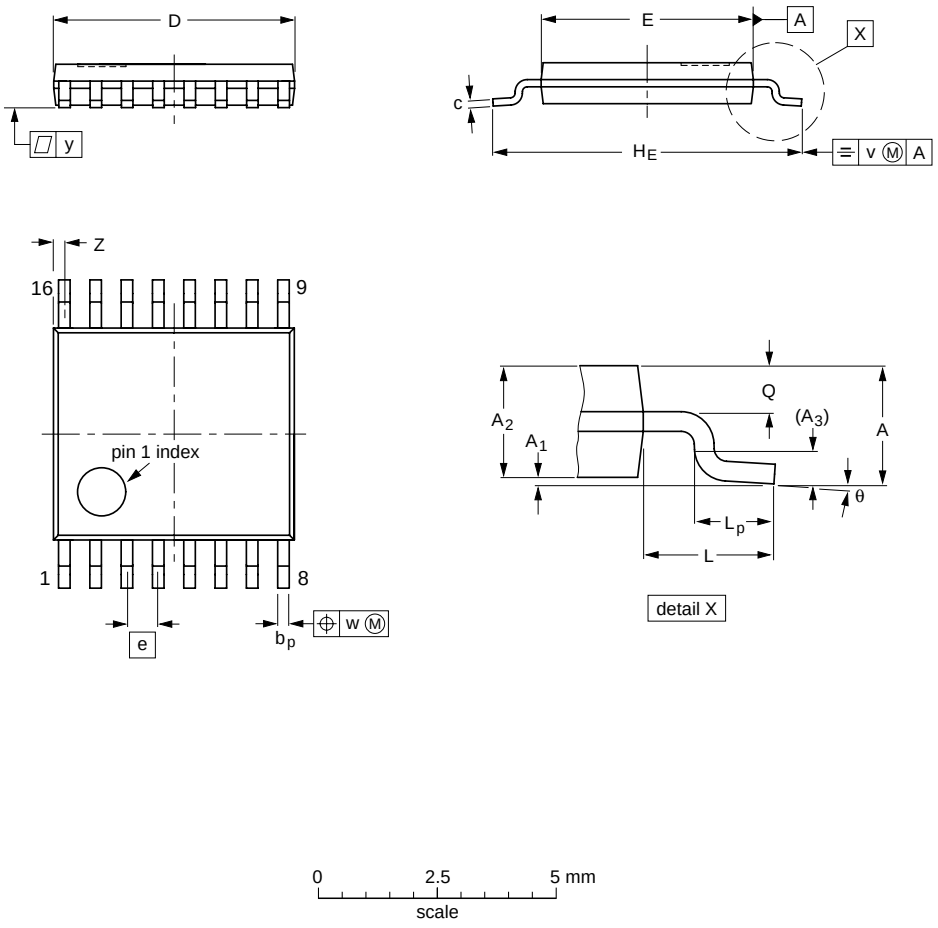
Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT109-1	076E07	MS-012				~~99-12-27~~ 03-02-19

Fig 8. Package outline SOT109-1 (SO16)

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm **SOT403-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (2)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.40 0.06	8^o 0^o

Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT403-1		MO-153				~~99-12-27~~ 03-02-18

Fig 9. Package outline SOT403-1 (TSSOP16)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
LSTTL	Low-power Schottky Transistor-Transistor Logic
MM	Machine Model

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC_AHCT139_2	20080509	Product data sheet	-	74AHC_AHCT139_1
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Table 6: the conditions for input leakage current have been changed.			
74AHC_AHCT139_1	19990901	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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